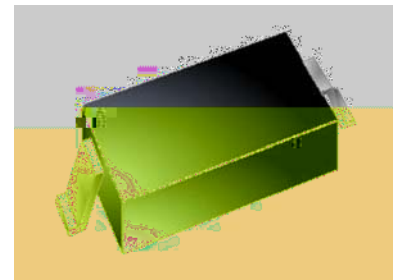
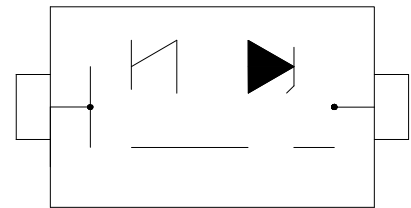




350 watts peak pulse power per line ($t_P=8/20\mu s$)
 Protects one bi-directional I/O line
 Low clamping voltage
 Working voltage: 15V
 Low leakage current
 RoHS compliant
 AEC-Q101 qualified



SOD-323



Pin Configuration

Cell phone handsets and accessories
 Microprocessor based equipment
 Personal digital assistants (PDA's)
 Notebooks, desktops, and servers
 Portable instrumentation
 Peripherals
 USB interface

IEC61000-4-2 (ESD) $\pm 30kV$ (air), $\pm 30kV$ (contact)
 IEC61000-4-4 (EFT) 40A (5/50ns)
 IEC61000-4-5 (lightning) 10A (8/20 μs)

SOD-323 package
 Molding compound flammability rating: UL 94V-0
 Quantity per reel: 3,000pcs
 Lead finish: lead free
 Marking code: BB

TVS Diode Array



JieJie Microelectronics Co., Ltd.

($T_A=25$, RH=45%-75%, unless otherwise r

Parameter	Symbol	Value	Unit
Peak pulse power dissipation at 8/20 μ s waveform	P_{PP}	3	W
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	+/ +/-	kV
Lead soldering temperature	T_L	260 (1	
Operating junction temperature range	T_J	-55 to	
Storage temperature range	T_{STG}	-55 to	

($T_A=25$)

Parameter	Symbol	Conditions	Min	Max	Unit
Reverse working voltage	V_{RWM}			15	V
Reverse breakdown voltage	V_{BR}	$I_T=1mA$	16.7		V
Reverse leakage current	I_R	$V_{RWM}=15V$		1	μA
Clamping voltage	V_C	$I_{PP}=1A, t_P=9$			

FIG.3: Pulse derating curve

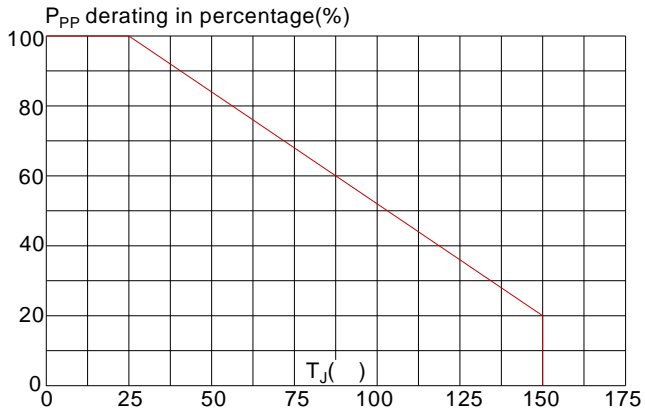
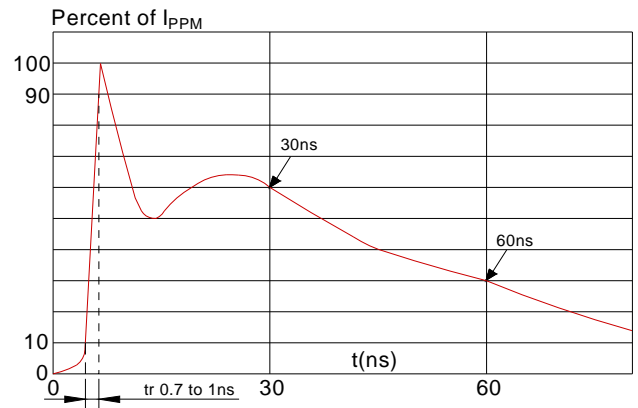


FIG.4: ESD clamping (30kV contact)



Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150
	-Temperature Max($T_{s(max)}$)	+200
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 /sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 /sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)
Time within 5% of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 /sec. Max
Time 25% to Peak Temp (T_p)		8 min. Max
Do not exceed		+260

